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Reference Number List

- 101 buried first semiconductor layer
- 103 recess
- 5 105' portion of recess
- 105'' further semiconductor area
- 107 top surface of the further semiconductor area
- 109 top surface of the buried first semiconductor layer
- 111 second semiconductor layer
- 10 113 semiconductor area
- 115 bottom surface of the semiconductor area
- 201 substrate
- 203 buried first semiconductor layer
- 204 buried first semiconductor layer
- 15 205 first recess
- 207 second recess
- 209 further semiconductor area
- 211 further semiconductor area
- 213 second semiconductor layer
- 20 214 deep trench isolation
- 215 first terminal
- 217 second terminal
- 219 base
- 221 further substrate layers
- 25 222 further substrate layers
- 223 emitter layer
- 225 base terminal layer
- 227 isolation layer
- 229 top surface of the second semiconductor area
- 30 231 top surface of the further second semiconductor area
- 301 SIC
- 401 bottom semiconductor area
- 701 substrate
- 801 substrate
- 35 803 subcollector
- 805 first SIC
- 807 second SIC
- 809 collector epitaxy

- 811 base
- 813 base terminal layer
- 815 emitter
- 817 passivation layer
- 5 819 oxide layer
- 820 terminal
- 821 further terminal
- 823 deep trench isolation
- 824 subcollector